

	Type	Hits	Search Text	DBs
1	BRS	16	"5,729,419"	US-PGPUB; USPAT
2	BRS	13	"5,901,022"	US-PGPUB; USPAT
3	BRS	1079	esd and clamp	US-PGPUB; USPAT
4	BRS	18	esd and clamp and p adj conductivity	US-PGPUB; USPAT
5	BRS	53	esd and p adj conductivity	US-PGPUB; USPAT
6	BRS	154	esd and p adj2 conductivity	US-PGPUB; USPAT
7	BRS	147	esd and p adj2 conductivity and well	US-PGPUB; USPAT
8	BRS	53	esd and p adj2 conductivity and (isolated isolating)	US-PGPUB; USPAT
9	BRS	24	esd and p adj2 conductivity and (isolated isolating) same well	US-PGPUB; USPAT
10	BRS	510	esd and p adj2 substrate and p adj2 well	US-PGPUB; USPAT
11	BRS	69	esd and p adj2 substrate and p adj2 well same (isolating isolated)	US-PGPUB; USPAT
12	BRS	69	esd and p adj2 substrate and (isolated isolating) same p adj2 well	US-PGPUB; USPAT
13	BRS	44	esd and p adj2 substrate and (isolated isolating) same p adj2 well and NMOS	US-PGPUB; USPAT
14	BRS	6	("5729419" "5901022" "5910874" "5945713" "6025746" "6128171").PN.	USPAT
15	BRS	3630	361/56	US-PGPUB; USPAT
16	BRS	13	"5,901,022"	US-PGPUB; USPAT
17	BRS	1	"5446311".PN.	USPAT
18	BRS	16	"5,729,419"	US-PGPUB; USPAT

	Time Stamp	Comments	Error Definition	Errors	Ref #
1	2004/02/16 11:00				S1
2	2004/02/11 11:50				S2
3	2004/02/12 11:24				S3
4	2004/02/11 11:51				S4
5	2004/02/11 11:51				S5
6	2004/02/11 11:52				S6
7	2004/02/12 14:07				S7
8	2004/02/11 11:52				S8
9	2004/02/11 14:13				S9
10	2004/02/11 14:14				S10
11	2004/02/11 14:15				S11
12	2004/02/11 14:15				S12
13	2004/02/11 16:10				S13
14	2004/02/11 15:47				S14
15	2004/02/11 16:10				S15
16	2004/02/12 11:34				S16
17	2004/02/12 11:34				S17
18	2004/02/12 11:52				S18

	Type	Hits	Search Text	DBs
19	BRS	15	("4456939" "4481521" "4678950" "4692834" "4739438" "4868705" "5019883" "5157571" "5208719" "5218222" "5287241" "5301081" "5333093" "5345356" "5379175").PN.	USPAT
20	BRS	1	"6,594,132"	US-PGPUB; USPAT
21	BRS	21	"5,959,820"	US-PGPUB; USPAT
22	BRS	21	"6,015,992"	US-PGPUB; USPAT
23	BRS	41	"5,287,241"	US-PGPUB; USPAT
24	BRS	9	esd and p adj2 conductivity and well and "3.3" adj (V volt volts)	US-PGPUB; USPAT
25	BRS	34	esd and "3.3" adj (V volt volts) same clamp	US-PGPUB; USPAT
26	BRS	2	esd and p adj2 conductivity and well and "3.3" adj (V volt volts) same clamp	US-PGPUB; USPAT
27	BRS	55	"4,782,250"	US-PGPUB; USPAT
28	BRS	2973	361/111	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
29	BRS	7	"6,184,557"	US-PGPUB; USPAT
30	BRS	7	"5,841,723"	US-PGPUB; USPAT
31	BRS	41	"5,287,241"	US-PGPUB; USPAT
32	BRS	14	"5,917,220"	US-PGPUB; USPAT
33	BRS	10	"5,477,413"	US-PGPUB; USPAT
34	BRS	658	361/91.1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
35	BRS	787	257/357	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors	Ref #
19	2004/02/12 11:35				S19
20	2004/02/12 11:54				S20
21	2004/02/12 11:55				S21
22	2004/02/12 12:23				S22
23	2004/02/12 12:23				S23
24	2004/02/12 14:08				S24
25	2004/02/12 15:37				S25
26	2004/02/12 14:08				S26
27	2004/02/12 15:37				S27
28	2004/02/12 16:41				S28
29	2004/02/13 10:54				S29
30	2004/02/13 11:23				S30
31	2004/02/13 12:05				S31
32	2004/02/13 14:57				S32
33	2004/02/13 14:57				S33
34	2004/02/13 15:42				S34
35	2004/02/16 11:01				S35

	Type	Hits	Search Text	DBs
36	BRS	1627	esd and (input output) same (protection protecting) and diode	US-PGPUB; USPAT
37	BRS	404	esd and (input output) same (protection protecting) and (plurality plural multiple) same (diode diodes)	US-PGPUB; USPAT
38	BRS	155	esd and (input output) same (protection protecting) same (plurality plural multiple) same (diode diodes)	US-PGPUB; USPAT
39	BRS	7	"6,046,897"	US-PGPUB; USPAT
40	BRS	15	("4063274" "4173022" "4272881" "4274193" "4423431" "4989057" "5144519" "5311391" "5399507" "5465189" "5477414" "5530612" "5539327" "5565790" "5726844").PN.	USPAT
41	BRS	45	"5,530,612"	US-PGPUB; USPAT
42	BRS	45	"5,530,612"	US-PGPUB; USPAT
43	BRS	4	"5,287,341"	US-PGPUB; USPAT
44	BRS	41	"5,287,241"	US-PGPUB; USPAT
45	BRS	8	"5,729,022"	US-PGPUB; USPAT
46	BRS	16	"5,729,419"	US-PGPUB; USPAT
47	BRS	684	esd and substrate same well same (mos mosfet fet field adj effect)	US-PGPUB; USPAT
48	BRS	28	esd and substrate same well same (mos mosfet fet field adj effect) same clamp	US-PGPUB; USPAT
49	BRS	192	esd and substrate same well same (mos mosfet fet field adj effect) same cmos	US-PGPUB; USPAT
50	BRS	477690	esd and substrate same well same (mos mosfet fet field adj effect) same cmos san clamp	US-PGPUB; USPAT

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36	2004/02/16 11:51				S36
37	2004/02/16 11:53				S37
38	2004/02/16 12:01				S38
39	2004/02/16 12:22				S39
40	2004/02/16 12:01				S40
41	2004/02/16 13:55				S41
42	2004/02/16 14:12				S42
43	2004/02/16 14:13				S43
44	2004/02/16 14:23				S44
45	2004/02/16 14:23				S45
46	2004/02/16 14:24				S46
47	2004/08/09 15:42				S47
48	2004/08/09 15:53				S48
49	2004/08/09 15:54				S49
50	2004/08/09 15:54				S50

	Type	Hits	Search Text	DBs
51	BRS	71	esd and substrate same well same (mos mosfet fet field adj effect) same cmos and clamp	US-PGPUB; USPAT
52	BRS	41	"5,262,344"	US-PGPUB; USPAT
53	BRS	7509	esd substrate same well same (mos mosfet fet field adj effect) same cmos and clamp	US-PGPUB; USPAT
54	BRS	7	substrate same well same (mos mosfet fet field adj effect) same cmos and esd adj clamp	US-PGPUB; USPAT
55	BRS	0	substrate same well same (mos mosfet fet field adj effect) same functional adj circuit and esd adj clamp	US-PGPUB; USPAT
56	BRS	0	substrate same well same (mos mosfet fet field adj effect) same logic adj (circuit stage) and esd adj clamp	US-PGPUB; USPAT
57	BRS	1	substrate same well same (mos mosfet fet field adj effect) and logic adj (circuit stage gate) and esd adj clamp	US-PGPUB; USPAT
58	BRS	2217	substrate same well same (mos mosfet fet field adj effect) and logic adj (circuit stage gate)	US-PGPUB; USPAT
59	BRS	333	substrate same well same (mos mosfet fet field adj effect) same logic adj (circuit stage gate)	US-PGPUB; USPAT
60	BRS	0	substrate same well same (mos mosfet fet field adj effect) same logic adj (circuit stage gate) and (mos mosfet fet field adj effect) adj inside adj well	US-PGPUB; USPAT
61	BRS	0	substrate same logic adj (circuit stage gate) and (mos mosfet fet field adj effect) adj inside adj well	US-PGPUB; USPAT
62	BRS	4	(mos mosfet fet field adj effect) adj inside adj well same substrate	US-PGPUB; USPAT
63	BRS	364	(mos mosfet fet field adj effect) same inside same well same substrate	US-PGPUB; USPAT

	Time Stamp	Comments	Error Definition	Errors	Ref #
51	2004/08/09 16:07				S51
52	2004/08/09 16:00				S52
53	2004/08/09 16:07				S53
54	2004/08/09 16:09				S54
55	2004/08/09 16:09				S55
56	2004/08/09 16:10				S56
57	2004/08/09 16:11				S57
58	2004/08/09 16:11				S58
59	2004/08/09 16:14				S59
60	2004/08/09 16:15				S60
61	2004/08/09 16:15				S61
62	2004/08/09 16:17				S62
63	2004/08/09 16:17				S63

	Type	Hits	Search Text	DBs
64	BRS	38	(mos mosfet fet field adj effect) same inside adj well same substrate	US-PGPUB; USPAT
65	BRS	2	(mos mosfet fet field adj effect) same substrate and inside adj well near transistor	US-PGPUB; USPAT
66	BRS	44	"5,287,241"	US-PGPUB; USPAT
67	BRS	16086	(mos mosfet fet field adj effect) same substrate same well	US-PGPUB; USPAT
68	BRS	2350	(mos mosfet fet field adj effect) same substrate same well same isolation	US-PGPUB; USPAT
69	BRS	3158	(mos mosfet fet field adj effect) same substrate same well same (isolation isolating isolated)	US-PGPUB; USPAT
70	BRS	996553	(mos mosfet fet field adj effect) same substrate same well same (isolation isolating isolated) aadj region	US-PGPUB; USPAT
71	BRS	861	(mos mosfet fet field adj effect) same substrate same well same (isolation isolating isolated) adj region	US-PGPUB; USPAT
72	BRS	8	(mos mosfet fet field adj effect) same substrate same well same (isolation isolating isolated) adj region and surrounding near well	US-PGPUB; USPAT
73	BRS	4220	361/56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
74	BRS	3349	361/111	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
75	BRS	2	esd adj2 substrate and p adj2 well same (isolating isolated)	US-PGPUB; USPAT
76	BRS	156	esd and p adj2 substrate same (isolating isolated)	US-PGPUB; USPAT
77	BRS	48	esd and p adj2 substrate same (isolating isolated) same p adj2 well	US-PGPUB; USPAT

	Time Stamp	Comments	Error Definition	Errors	Ref #
64	2004/08/09 16:24				S64
65	2004/08/09 16:25				S65
66	2004/08/10 09:23				S66
67	2004/08/10 09:24				S67
68	2004/08/10 09:24				S68
69	2004/08/10 09:25				S69
70	2004/08/10 09:25				S70
71	2004/08/10 09:25				S71
72	2004/08/10 09:26				S72
73	2004/12/13 10:43				S73
74	2004/12/13 13:13				S74
75	2004/12/13 13:43				S75
76	2004/12/13 13:44				S76
77	2004/12/13 13:44				S77

	Type	Hits	Search Text	DBs
78	BRS	8	esd and p adj2 substrate same (isolating isolated) same p adj2 well and (trigger triggering) same (capacitor capacitive)	US-PGPUB; USPAT
79	BRS	5	("5341005" "5508548" "5945713" "6043969" "6233130").PN.	US-PGPUB; USPAT; USOCR
80	BRS	258	361/91.7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
81	BRS	885	257/357	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Time Stamp	Comments	Error Definition	Errors	Ref #
78	2004/12/13 13:45				S78
79	2004/12/13 13:59				S79
80	2004/12/13 15:28				S80
81	2004/12/13 16:06				S81